TECHNICAL DATA DATA SHEET 779, REV. B

HERMETIC POWER SCHOTTKY RECTIFIER Ultra Low Reverse Leakage 200°C Operating Temperature

Applications:

• Switching Power Supply • Converters • Free-Wheeling Diodes • Polarity Protection Diode

Features:

- Ultra low Reverse Leakage Current
- Soft Reverse Recovery at Low and High Temperature
- Very Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics
- Out Performs 100 Volt Ultrafast Rectifiers

Maximum Ratings:

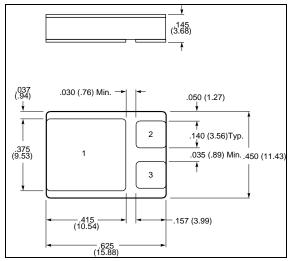
Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	100	V
Max. Average Forward Current	I _{F(AV)}	50% duty cycle, rectangular wave form (Single)	15	А
Max. Average Forward Current	I _{F(AV)}	50% duty cycle, rectangular wave form (Common Cathode)	30	A
Max. Peak One Cycle Non- Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine wave (per leg)	200	А
Max. Thermal Resistance	$R_{\theta JC}$	(Single)	2.65	°C/W
Max. Junction Temperature	T _J	-	-65 to +200	°C
Max. Storage Temperature	T _{stg}	-	-65 to +175	°C

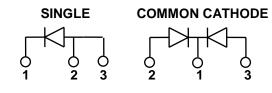
Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V_{F1}	@ 15A, Pulse, T _J = 25 °C	0.93	V
		(per leg)		
	V_{F2}	@ 15A, Pulse, T _J = 125 °C	0.77	V
		(per leg)		
Max. Reverse Current	I_{R1}	@V _R = 100V, Pulse,	.1	mA
		$T_J = 25 ^{\circ}\text{C} \text{ (per leg)}$		
	I_{R2}	@V _R = 100V, Pulse,	1.0	mA
		$T_J = 125 ^{\circ}\text{C} \text{ (per leg)}$		
Max. Junction Capacitance	C _T	@V _R = 5V, T _C = 25 °C	500	pF
		$f_{SIG} = 1MHz,$		
		$V_{SIG} = 50 \text{mV (p-p) (per leg)}$		

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MECHANICAL DIMENSIONS: IN Inches / mm



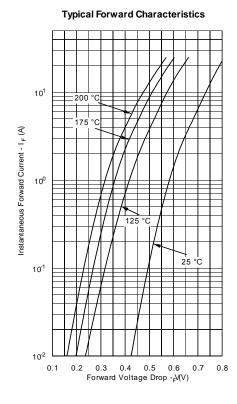


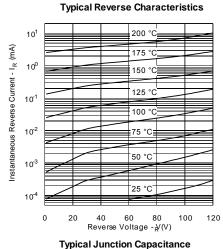
LCC-3P

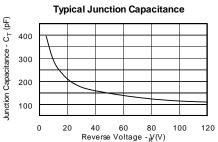
PINOUT TABLE

DEVICE TYPE	PIN 1	PIN 2	PIN 3
SINGLE RECTIFIER	CATHODE	ANODE	ANODE
COMMON CATHODE	COMMON CATHODE	ANODE 1	ANODE 2

Note: The V_f curves shown are for the SD125SCU100 unpackaged die only.







SENSITRON

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